

# ANTREX Electronics

## Electronic Components Sourcing Information

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### Product Reference Information

|                      |                           |
|----------------------|---------------------------|
| <b>Part Number:</b>  | C3M0025065L-TR            |
| <b>Manufacturer:</b> | Wolfspeed, Inc.           |
| <b>Package:</b>      | Please confirm with sales |
| <b>Availability:</b> | Please confirm with sales |

#### Product Page:

<https://antrexco.com/product/details/wolfspeed-inc/c3m0025065l-tr.html>

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#### Note:

This PDF includes an ANTREX product reference cover page.

The original manufacturer datasheet follows from the next page.

# C3M0025065L

Silicon Carbide Power MOSFET

C3M™ MOSFET Technology

N-Channel Enhancement Mode

## Features

- 3rd generation SiC MOSFET technology
- Optimized package with separate driver source pin
- High blocking voltage with low on-resistance
- High-speed switching with low capacitances
- Fast intrinsic diode with low reverse recovery ( $Q_{rr}$ )
- Halogen free, RoHS compliant

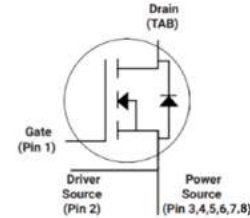
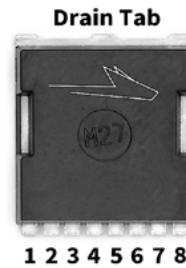
## Benefits

- Reduce switching losses and minimize gate ringing
- Higher system efficiency
- Reduce cooling requirements
- Increase power density
- Increase system switching frequency

## Typical Applications

- Datacenter Power Supplies
- Telecom Power Supplies
- Energy Storage Systems
- Solar (PV) inverters
- High Voltage DC/DC converters

## Package



| Orderable Part Number | Package | Marking     |
|-----------------------|---------|-------------|
| C3M0025065L-TR        | TOLL    | C3M0025065L |

Wolfspeed, Inc. is in the process of rebranding its products and related materials pursuant to the entity name change from Cree, Inc. to Wolfspeed, Inc. During this transition period, products received may be marked with either the Cree name and/or logo or the Wolfspeed name and/or logo.

## Key Parameters

| Parameter                                  | Symbol         | Min. | Typ.  | Max         | Unit             | Conditions                                                                         | Note    |
|--------------------------------------------|----------------|------|-------|-------------|------------------|------------------------------------------------------------------------------------|---------|
| Drain - Source Voltage                     | $V_{DS}$       |      |       | 650         | V                | $T_c = 25^\circ\text{C}$                                                           |         |
| Maximum Gate - Source Voltage              | $V_{GS(max)}$  | -8   |       | +19         |                  | Transient                                                                          |         |
| Operational Gate-Source Voltage            | $V_{GSop}$     |      | -4/15 |             |                  | Static                                                                             | Note 1  |
| DC Continuous Drain Current                | $I_D$          |      |       | 77          | A                | $V_{GS} = 15\text{ V}, T_c = 25^\circ\text{C}, T_J \leq 175^\circ\text{C}$         | Fig. 19 |
|                                            |                |      |       | 59          |                  | $V_{GS} = 15\text{ V}, T_c = 100^\circ\text{C}, T_J \leq 175^\circ\text{C}$        | Note 2  |
| Pulsed Drain Current                       | $I_{DM}$       |      |       | 235         |                  | $t_{pmax}$ limited by $T_{Jmax}$<br>$V_{GS} = 15\text{ V}, T_c = 25^\circ\text{C}$ | Fig. 22 |
| Power Dissipation                          | $P_D$          |      |       | 326         | W                | $T_c = 25^\circ\text{C}, T_J = 175^\circ\text{C}$                                  | Fig. 20 |
| Operating Junction and Storage Temperature | $T_J, T_{stg}$ |      |       | -40 to +175 | $^\circ\text{C}$ |                                                                                    |         |
| Solder Temperature                         | $T_L$          |      |       | 260         |                  | According to JEDEC J-STD-020                                                       |         |

Note (1): Recommended turn-on gate voltage is 15V with  $\pm 5\%$  regulation tolerance, see Application Note PRD-04814 for additional details

Note (2): Verified by design


**Electrical Characteristics** ( $T_c = 25^\circ\text{C}$  unless otherwise specified)

| Symbol        | Parameter                                     | Min. | Typ. | Max. | Unit          | Test Conditions                                                                                                                                                                                     | Note         |
|---------------|-----------------------------------------------|------|------|------|---------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|--------------|
| $V_{(BR)DSS}$ | Drain-Source Breakdown Voltage                | 650  |      |      | V             | $V_{GS} = 0\text{ V}, I_D = 100\text{ }\mu\text{A}$                                                                                                                                                 |              |
| $V_{GS(th)}$  | Gate Threshold Voltage                        | 1.8  | 2.3  | 3.6  | V             | $V_{DS} = V_{GS}, I_D = 9.22\text{ mA}$                                                                                                                                                             | Fig. 11      |
|               |                                               |      | 1.9  |      | V             | $V_{DS} = V_{GS}, I_D = 9.22\text{ mA}, T_J = 175^\circ\text{C}$                                                                                                                                    |              |
| $I_{DSS}$     | Zero Gate Voltage Drain Current               |      | 1    | 50   | $\mu\text{A}$ | $V_{DS} = 650\text{ V}, V_{GS} = 0\text{ V}$                                                                                                                                                        |              |
| $I_{GSS}$     | Gate-Source Leakage Current                   |      | 10   | 250  | nA            | $V_{GS} = 15\text{ V}, V_{DS} = 0\text{ V}$                                                                                                                                                         |              |
| $R_{DS(on)}$  | Drain-Source On-State Resistance              |      | 25   | 34   | m $\Omega$    | $V_{GS} = 15\text{ V}, I_D = 33.5\text{ A}$                                                                                                                                                         | Fig. 4, 5, 6 |
|               |                                               |      | 33   |      |               | $V_{GS} = 15\text{ V}, I_D = 33.5\text{ A}, T_J = 175^\circ\text{C}$                                                                                                                                |              |
| $g_{fs}$      | Transconductance                              |      | 24   |      | S             | $V_{DS} = 20\text{ V}, I_{DS} = 33.5\text{ A}$                                                                                                                                                      | Fig. 7       |
|               |                                               |      | 23   |      |               | $V_{DS} = 20\text{ V}, I_{DS} = 33.5\text{ A}, T_J = 175^\circ\text{C}$                                                                                                                             |              |
| $C_{iss}$     | Input Capacitance                             |      | 2970 |      | pF            | $V_{GS} = 0\text{ V}, V_{DS} = 400\text{ V}$<br>$f = 1\text{ MHz}$<br>$V_{AC} = 25\text{ mV}$                                                                                                       | Fig. 17, 18  |
| $C_{oss}$     | Output Capacitance                            |      | 186  |      |               |                                                                                                                                                                                                     |              |
| $C_{rss}$     | Reverse Transfer Capacitance                  |      | 11   |      |               |                                                                                                                                                                                                     |              |
| $E_{oss}$     | $C_{oss}$ Stored Energy                       |      | 18   |      | $\mu\text{J}$ | $V_{DS} = 400\text{ V}, f = 1\text{ MHz}$                                                                                                                                                           |              |
| $C_{o(er)}$   | Effective Output Capacitance (Energy Related) |      | 226  |      | pF            | $V_{GS} = 0\text{ V}, V_{DS} = 0 \dots 400\text{ V}$                                                                                                                                                | Note: 3      |
| $C_{o(tr)}$   | Effective Output Capacitance (Time Related)   |      | 322  |      | pF            |                                                                                                                                                                                                     |              |
| $E_{ON}$      | Turn-On Switching Energy (Body Diode FWD)     |      | 123  |      | $\mu\text{J}$ | $V_{DS} = 400\text{ V}, V_{GS} = -4\text{ V}/15\text{ V}, I_D = 33.5\text{ A},$<br>$R_{G(ext)} = 2.5\text{ }\Omega, L = 59\text{ }\mu\text{H}, T_J = 25^\circ\text{C}$<br>FWD = Internal Body Diode | Fig. 23      |
| $E_{OFF}$     | Turn-Off Switching Energy (Body Diode FWD)    |      | 14   |      |               |                                                                                                                                                                                                     |              |
| $t_{d(on)}$   | Turn-On Delay Time                            |      | 10   |      | ns            | $V_{DD} = 400\text{ V}, V_{GS} = -4\text{ V}/15\text{ V}$<br>$I_D = 33.5\text{ A}, R_{G(ext)} = 2.5\text{ }\Omega,$<br>Timing relative to $V_{DS}$<br>Inductive load                                | Fig. 26      |
| $t_r$         | Rise Time                                     |      | 13   |      |               |                                                                                                                                                                                                     |              |
| $t_{d(off)}$  | Turn-Off Delay Time                           |      | 26   |      |               |                                                                                                                                                                                                     |              |
| $t_f$         | Fall Time                                     |      | 8    |      |               |                                                                                                                                                                                                     |              |
| $R_{G(int)}$  | Internal Gate Resistance                      |      | 1.3  |      | $\Omega$      | $f = 1\text{ MHz}, V_{AC} = 25\text{ mV}$                                                                                                                                                           |              |
| $Q_{gs}$      | Gate to Source Charge                         |      | 33   |      | nC            | $V_{DS} = 400\text{ V}, V_{GS} = -4\text{ V}/15\text{ V}$<br>$I_D = 33.5\text{ A}$<br>Per IEC60747-8-4 pg 21                                                                                        | Fig. 12      |
| $Q_{gd}$      | Gate to Drain Charge                          |      | 32   |      |               |                                                                                                                                                                                                     |              |
| $Q_g$         | Total Gate Charge                             |      | 111  |      |               |                                                                                                                                                                                                     |              |

Note (3):  $C_{o(er)}$ , a lumped capacitance that gives same stored energy as  $C_{oss}$  while  $V_{ds}$  is rising from 0 to 400V

$C_{o(tr)}$ , a lumped capacitance that gives same charging time as  $C_{oss}$  while  $V_{ds}$  is rising from 0 to 400V



Reverse Diode Characteristics (T<sub>c</sub> = 25°C unless otherwise specified)

| Symbol                | Parameter                        | Typ. | Max. | Unit | Test Conditions                                                                                                        | Note          |
|-----------------------|----------------------------------|------|------|------|------------------------------------------------------------------------------------------------------------------------|---------------|
| V <sub>SD</sub>       | Diode Forward Voltage            | 5.0  |      | V    | V <sub>GS</sub> = -4 V, I <sub>SD</sub> = 16.8 A, T <sub>J</sub> = 25 °C                                               | Fig. 8, 9, 10 |
|                       |                                  | 4.4  |      | V    | V <sub>GS</sub> = -4 V, I <sub>SD</sub> = 16.8 A, T <sub>J</sub> = 175 °C                                              |               |
| I <sub>S</sub>        | Continuous Diode Forward Current |      | 54   | A    | V <sub>GS</sub> = -4 V, T <sub>c</sub> = 25°C                                                                          |               |
| I <sub>S, pulse</sub> | Diode pulse Current              |      | 235  | A    | V <sub>GS</sub> = -4 V, pulse width t <sub>p</sub> limited by T <sub>Jmax</sub>                                        |               |
| t <sub>rr</sub>       | Reverse Recover time             | 14   |      | ns   | V <sub>GS</sub> = -4 V, I <sub>SD</sub> = 33.5 A, V <sub>R</sub> = 400 V<br>dif/dt = 4717 A/μs, T <sub>J</sub> = 25 °C |               |
| Q <sub>rr</sub>       | Reverse Recovery Charge          | 338  |      | nC   |                                                                                                                        |               |
| I <sub>rrm</sub>      | Peak Reverse Recovery Current    | 40   |      | A    |                                                                                                                        |               |
| t <sub>rr</sub>       | Reverse Recover time             | 16   |      | ns   | V <sub>GS</sub> = -4 V, I <sub>SD</sub> = 33.5 A, V <sub>R</sub> = 400 V<br>dif/dt = 2137 A/μs, T <sub>J</sub> = 25 °C |               |
| Q <sub>rr</sub>       | Reverse Recovery Charge          | 164  |      | nC   |                                                                                                                        |               |
| I <sub>rrm</sub>      | Peak Reverse Recovery Current    | 17   |      | A    |                                                                                                                        |               |

Thermal Characteristics

| Symbol           | Parameter                                | Typ. | Max. | Unit | Note |
|------------------|------------------------------------------|------|------|------|------|
| R <sub>θJC</sub> | Thermal Resistance from Junction to Case | 0.41 | 0.46 | °C/W |      |



## Typical Performance

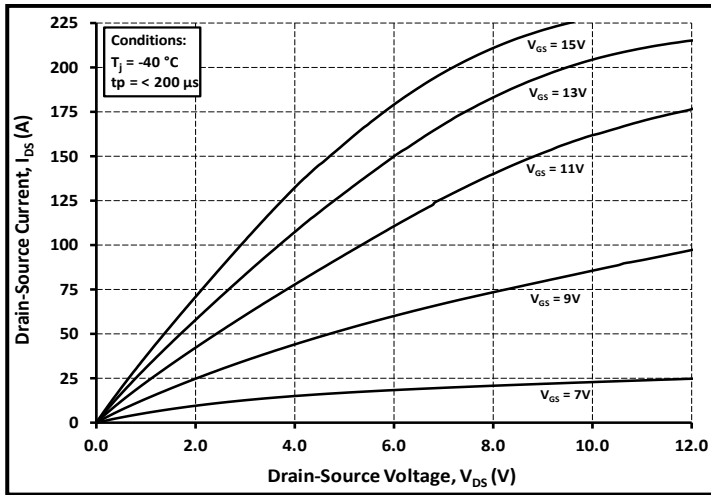


Figure 1. Output Characteristics  $T_J = -40\text{ }^{\circ}\text{C}$

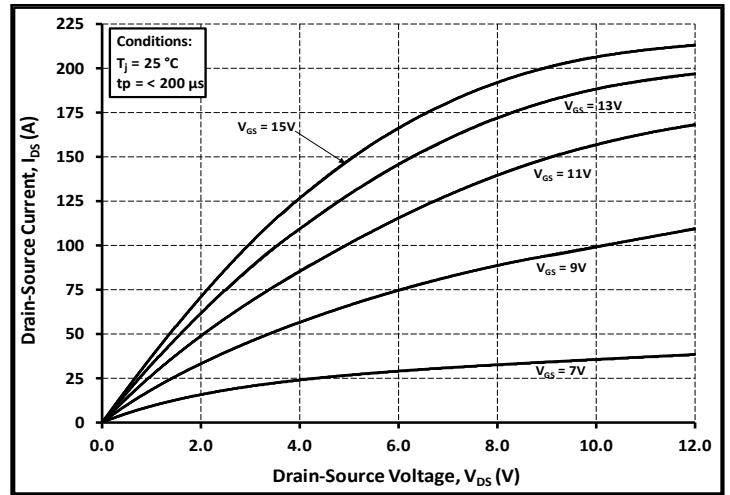


Figure 2. Output Characteristics  $T_J = 25\text{ }^{\circ}\text{C}$

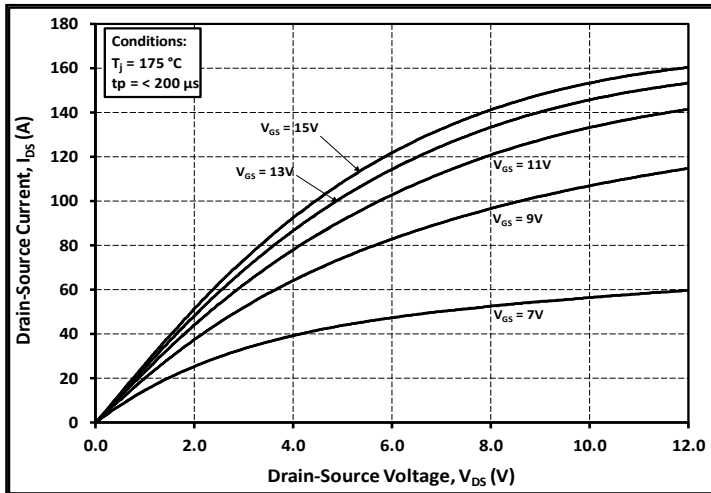


Figure 3. Output Characteristics  $T_J = 175\text{ }^{\circ}\text{C}$

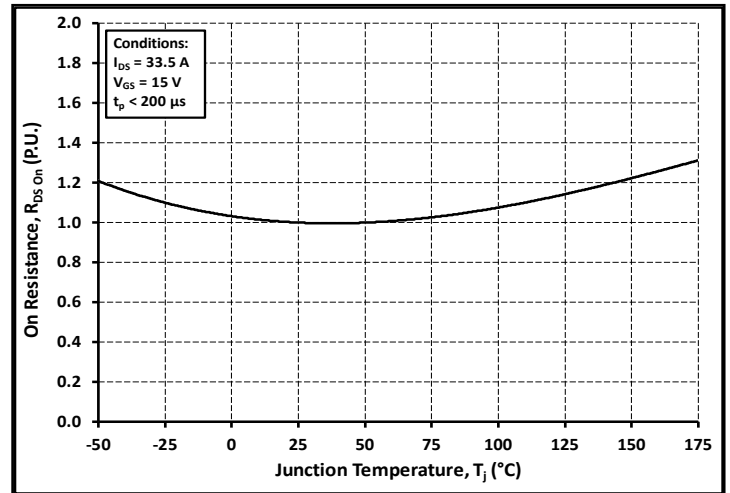


Figure 4. Normalized On-Resistance vs. Temperature

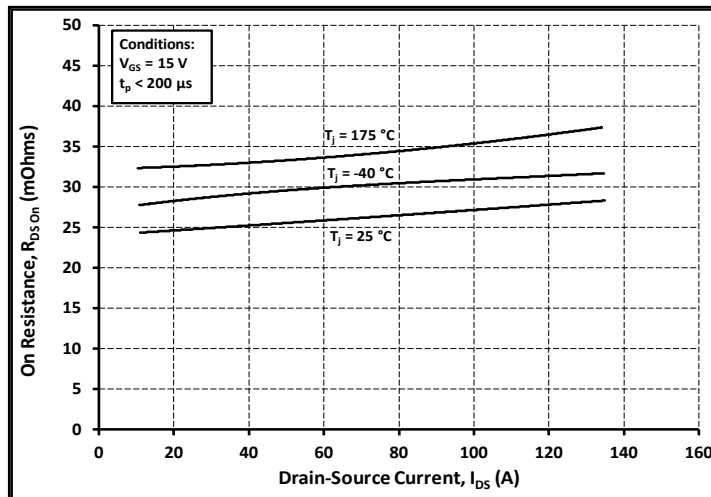


Figure 5. On-Resistance vs. Drain Current  
For Various Temperatures

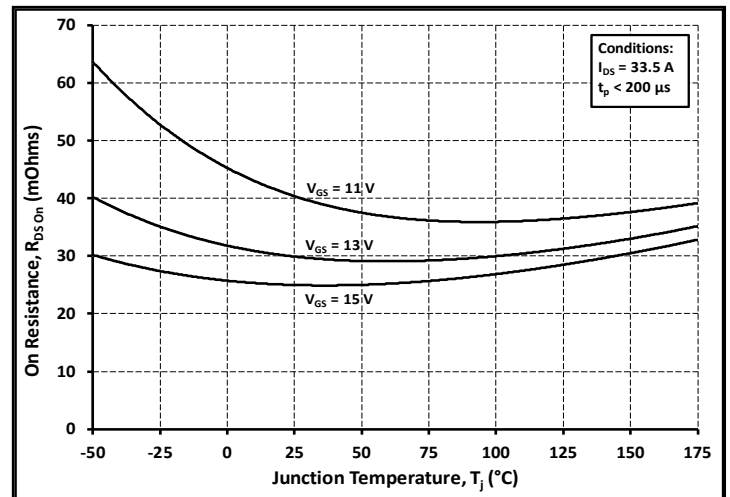


Figure 6. On-Resistance vs. Temperature  
For Various Gate Voltage

## Typical Performance

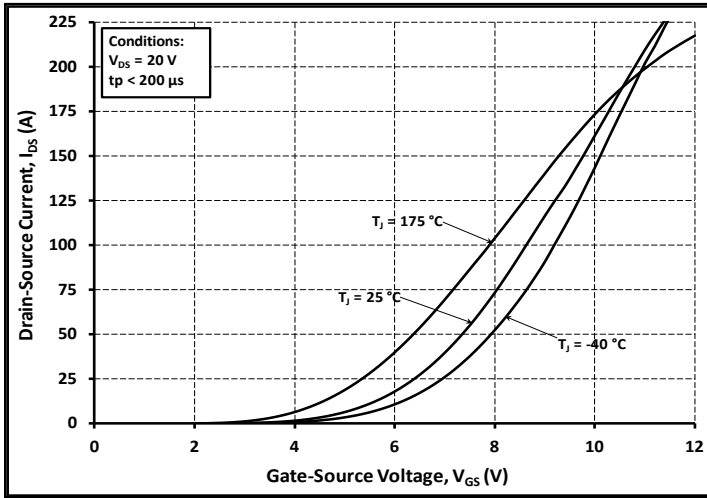


Figure 7. Transfer Characteristic for Various Junction Temperatures

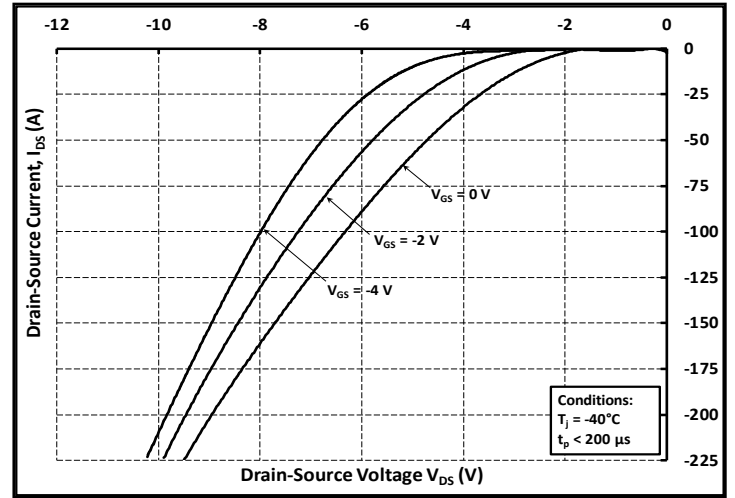


Figure 8. Body Diode Characteristic at -40 °C

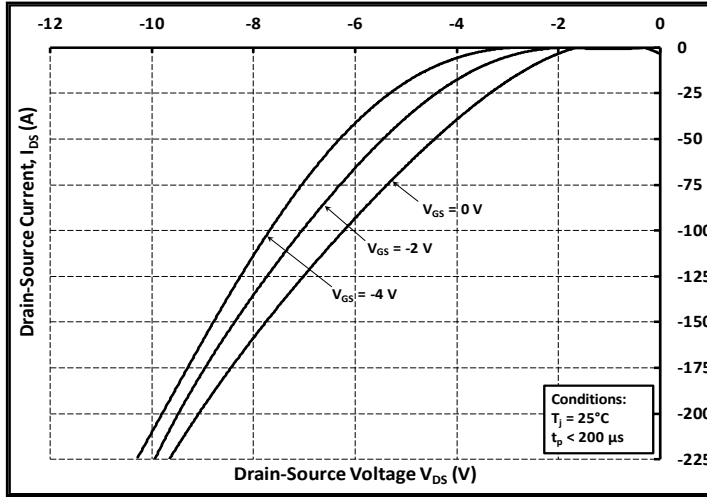


Figure 9. Body Diode Characteristic at 25 °C

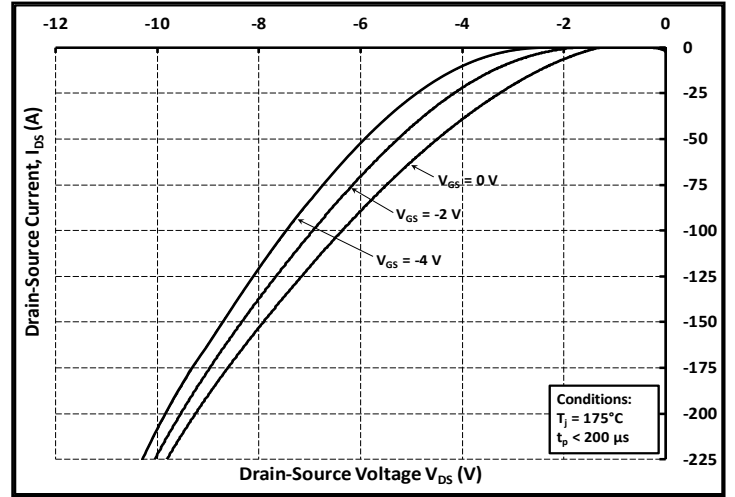


Figure 10. Body Diode Characteristic at 175 °C

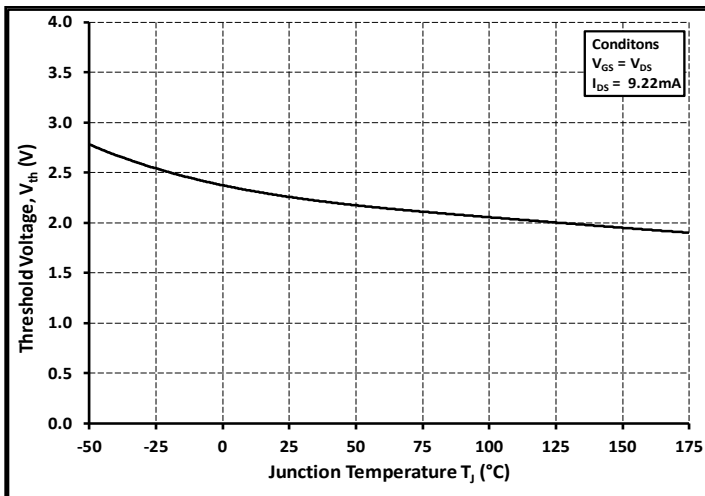


Figure 11. Threshold Voltage vs. Temperature

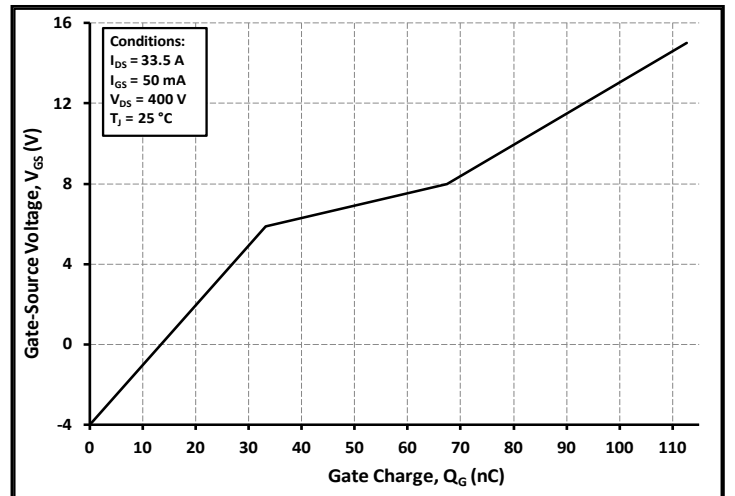


Figure 12. Gate Charge Characteristics

## Typical Performance

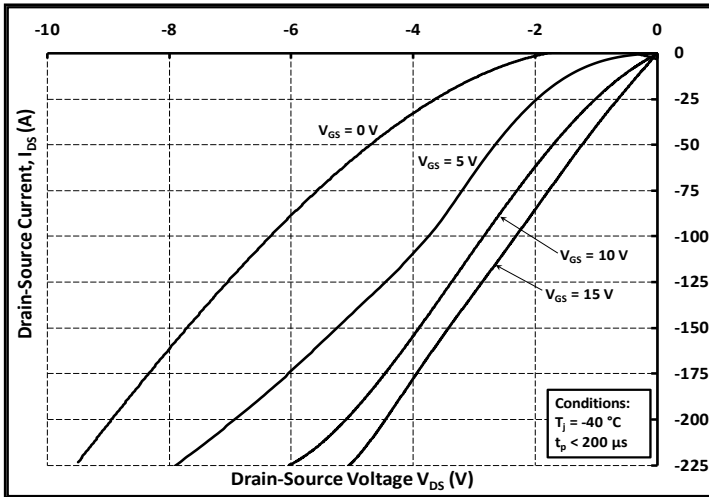
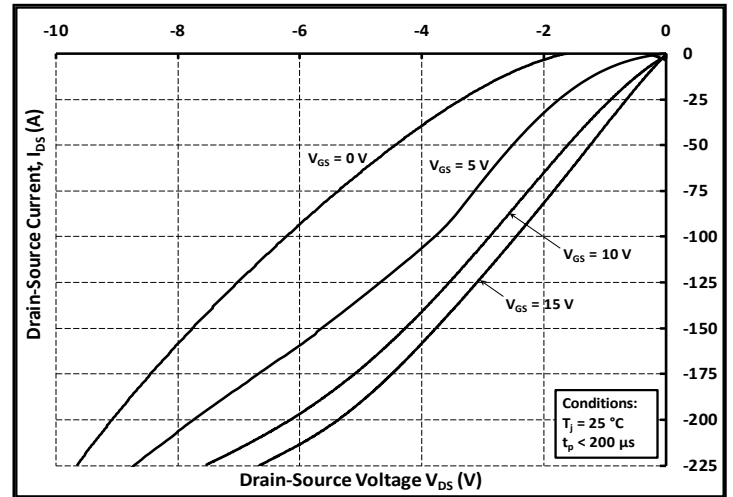
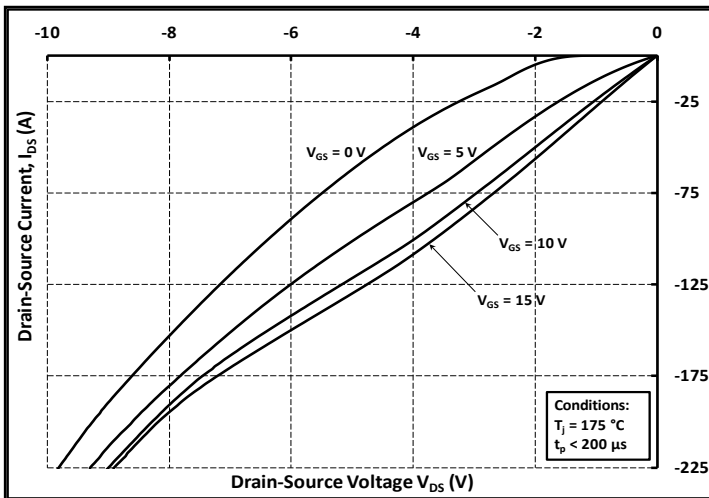
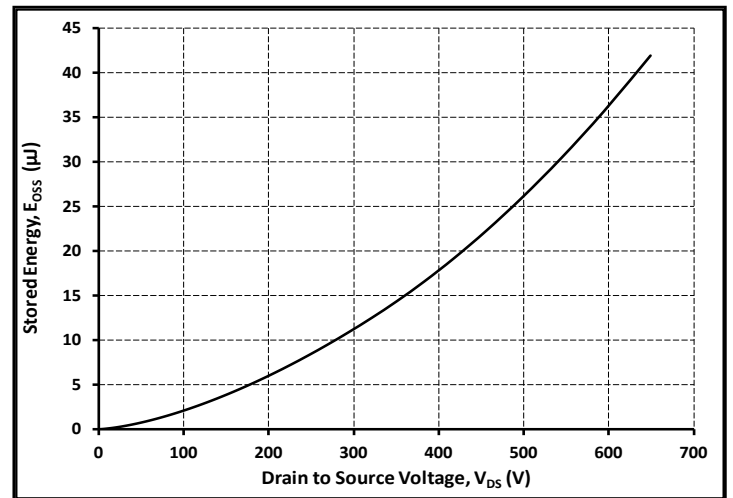
Figure 13. 3rd Quadrant Characteristic at  $-40\text{ }^{\circ}\text{C}$ Figure 14. 3rd Quadrant Characteristic at  $25\text{ }^{\circ}\text{C}$ Figure 15. 3rd Quadrant Characteristic at  $175\text{ }^{\circ}\text{C}$ 

Figure 16. Output Capacitor Stored Energy

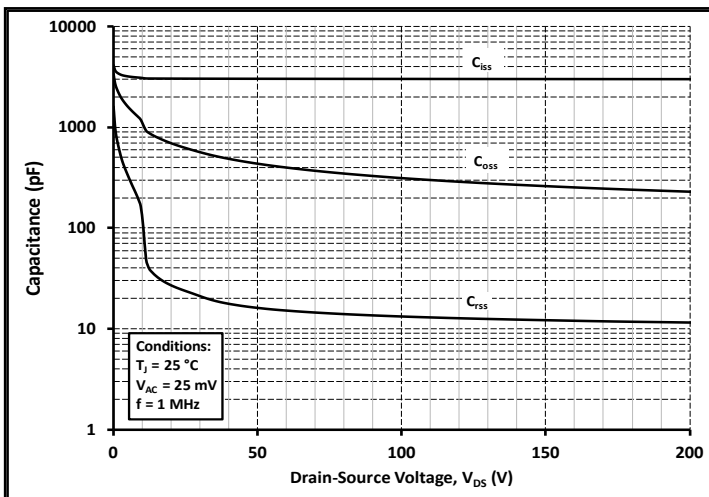


Figure 17. Capacitances vs. Drain-Source Voltage (0 - 200V)

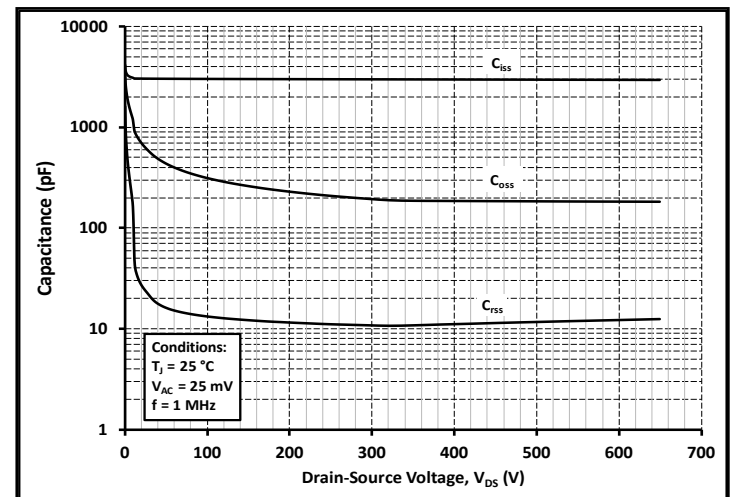


Figure 18. Capacitances vs. Drain-Source Voltage (0 - 650V)

## Typical Performance

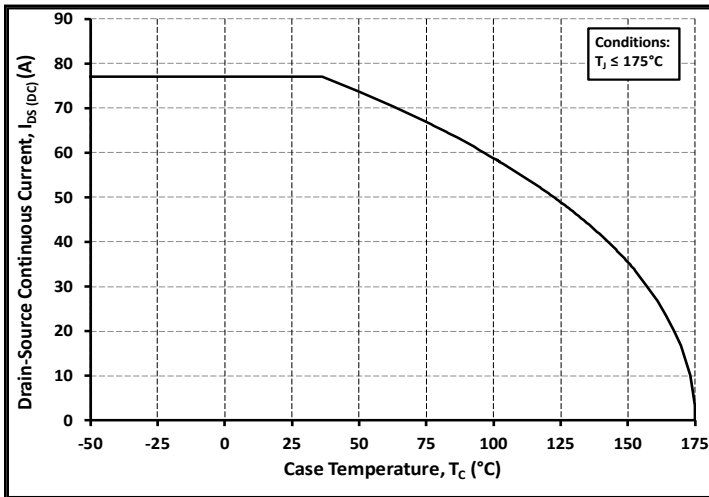


Figure 19. Continuous Drain Current Derating vs. Case Temperature

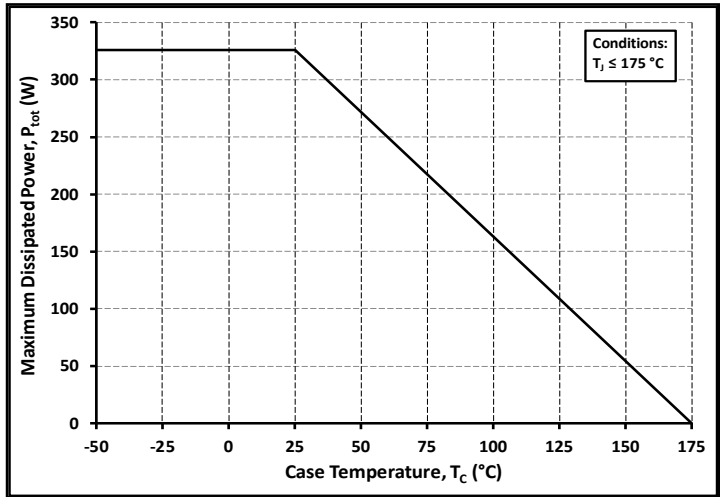


Figure 20. Maximum Power Dissipation Derating vs. Case Temperature

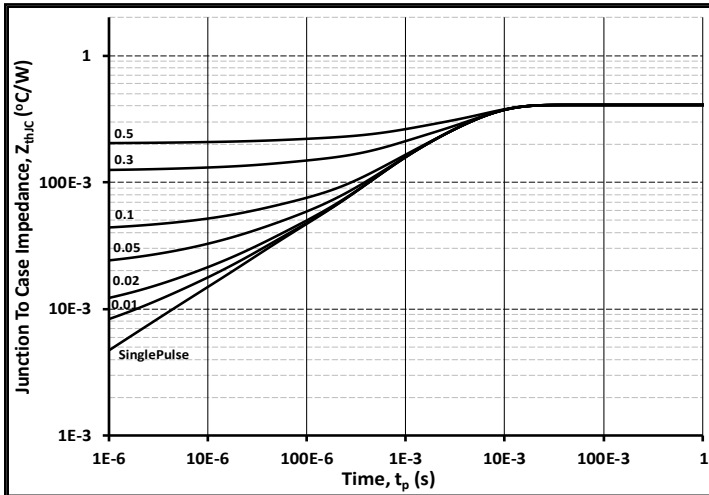


Figure 21. Transient Thermal Impedance (Junction - Case)

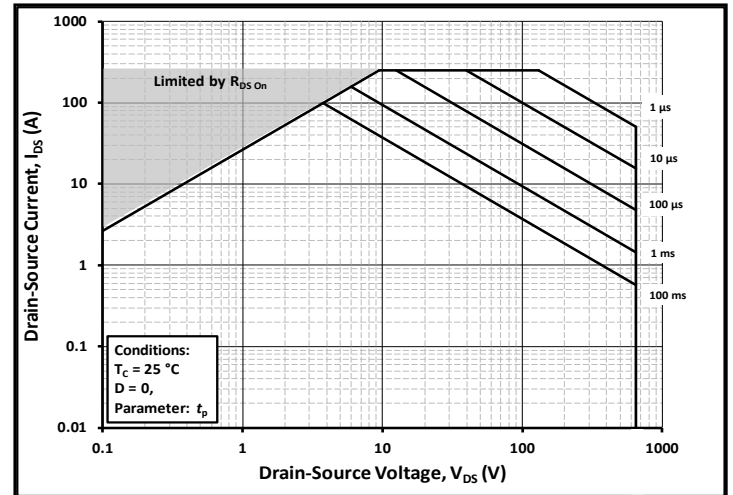
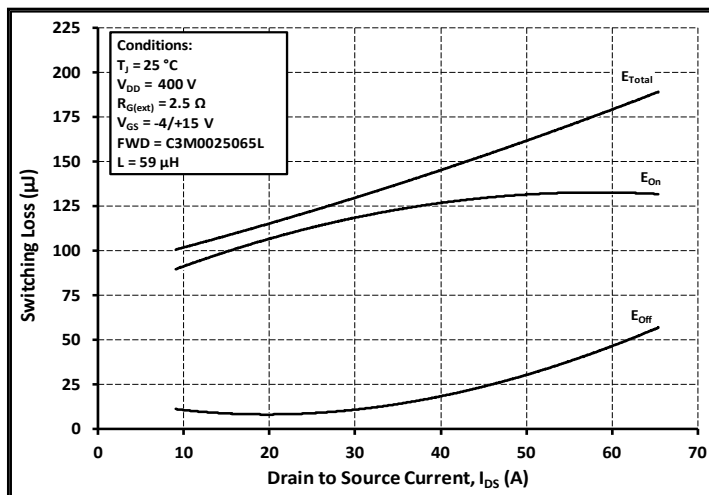
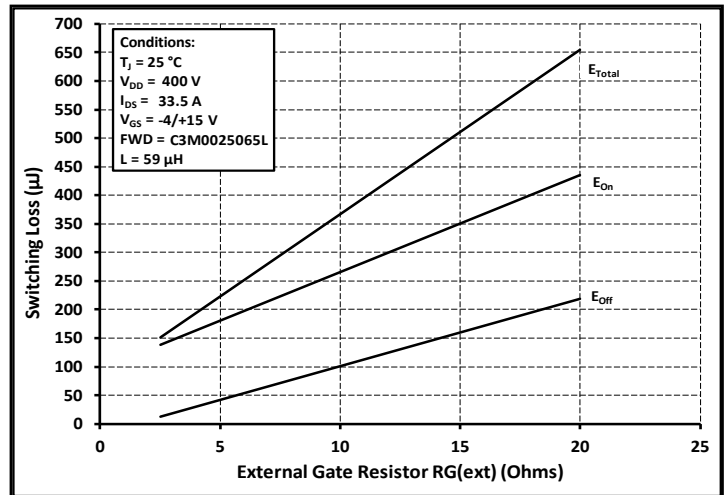


Figure 22. Safe Operating Area

Figure 23. Clamped Inductive Switching Energy vs. Drain Current ( $V_{DD} = 400V$ )Figure 24. Clamped Inductive Switching Energy vs.  $R_{G(ext)}$



Typical Performance

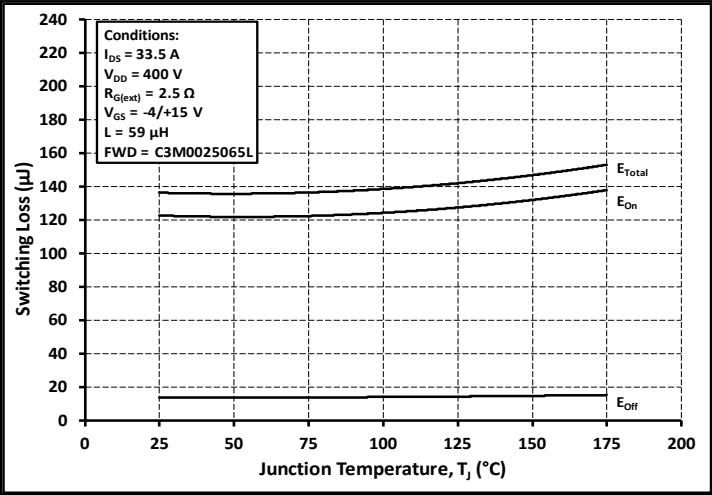


Figure 25. Clamped Inductive Switching Energy vs. Temperature

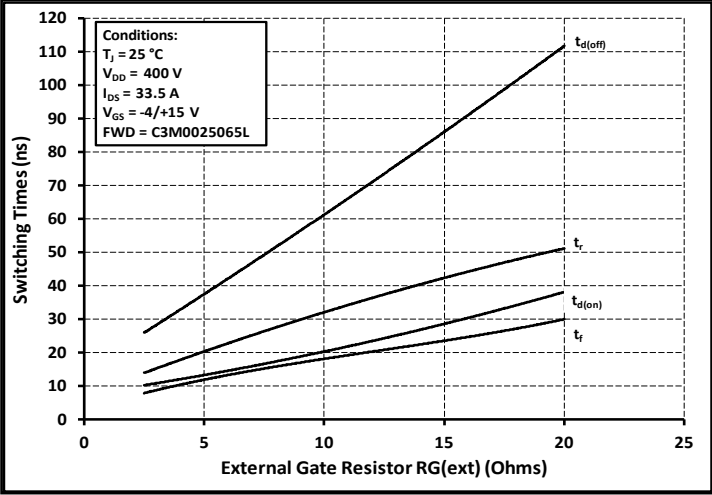


Figure 26. Switching Times vs.  $R_{G(ext)}$

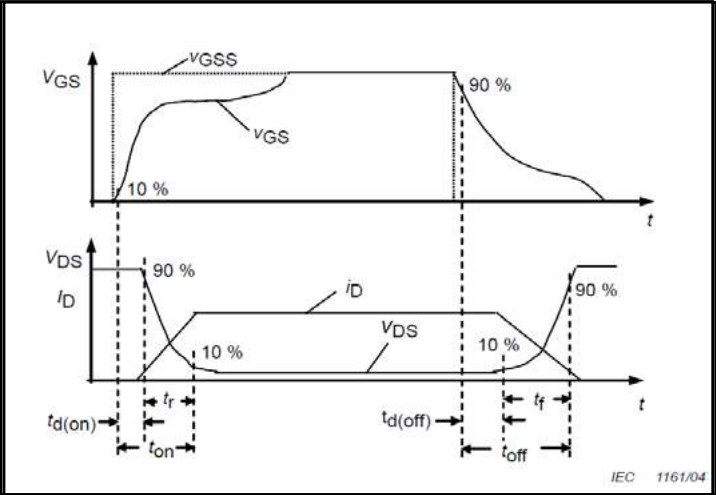


Figure 27. Switching Times Definition

## Test Circuit Schematic

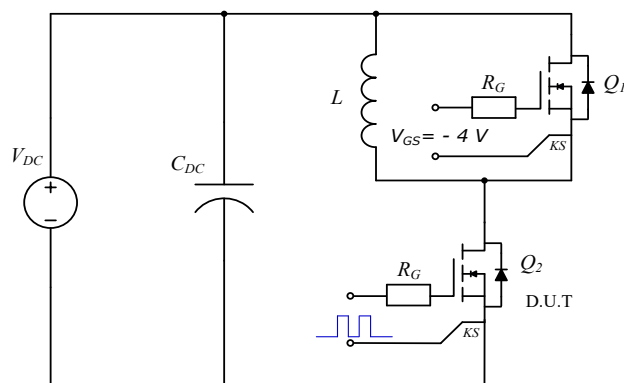
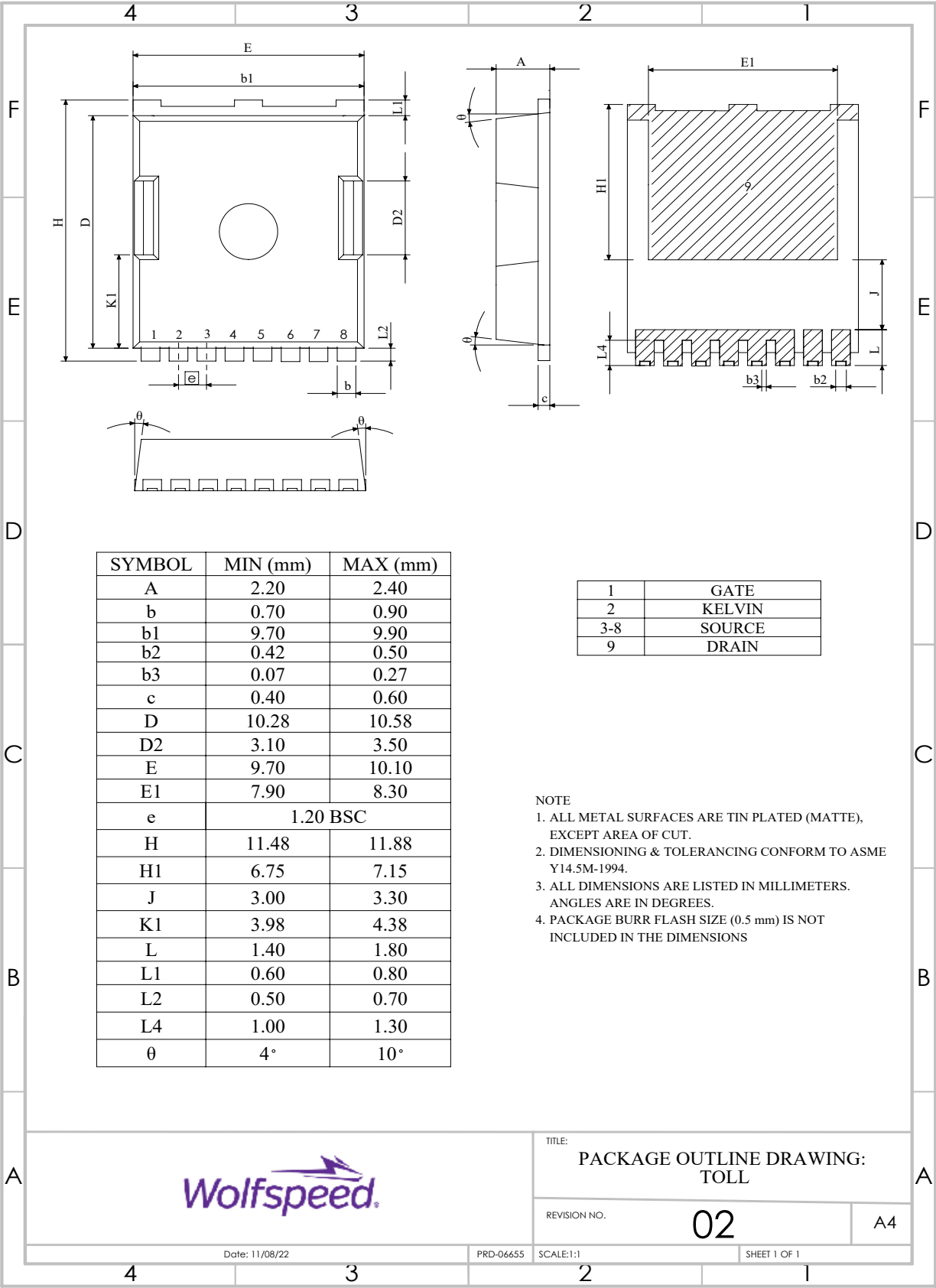


Figure 28. Clamped Inductive Switching  
Waveform Test Circuit

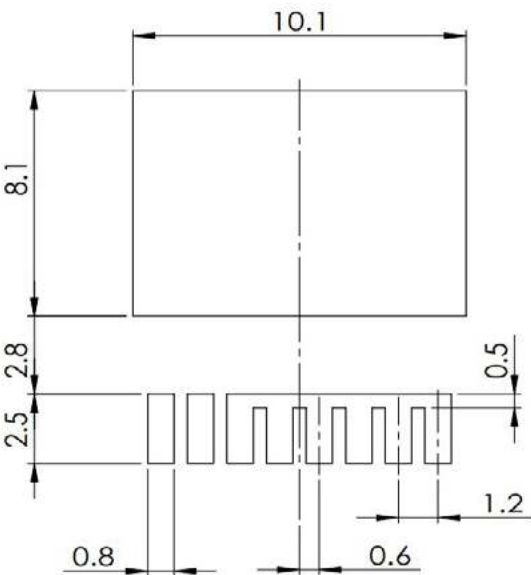
Package Dimensions





Recommended Solder Pad Layout

(Note: All Dimensions are listed in Millimeters)





**Revision history**

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| Document Version | Date of release | Description of changes                   |
|------------------|-----------------|------------------------------------------|
| 1                | October-2022    | Initial datasheet                        |
| 2                | December - 2024 | Legal Disclaimer, Table 1 layout revised |



## Notes & Disclaimer

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